NSN 5962-01-506-2728

Memory Microcircuit - Page 1 of 1



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Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Alq135 band 1
Inclosure Material:
Ceramic
Inclosure Configuration:
Leaded chip carrier
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Current Rating Per Characteristic:
20.00 milliamperes average forward current averaged over a full 60-hz cycle not applicable
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, cmos, 2k x 9 first-in first-out, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts applied and 7.0 volts applied
Memory Device Type:
First-in first-out
Hybrid Technology Type:
Monolithic
Memory Capacity:
Cmos, 2k x 9 first-in, first-ou (fifo)
Terminal Type And Quantity:
32 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A458a0